Silicon NPN Power Transistors BU508AF

DESCRIPTION

- With TO-3PFa package
- High voltage
- High speed switching

APPLICATIONS

- For use in horizontal deflection circuits of high resolution monitors

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

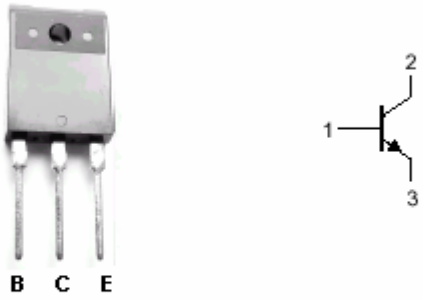

Fig.1 simplified outline (TO-3PFa) and symbol

Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{CEO}	Collector-emitter voltage	Open base	700	V
V_{EBO}	Emitter-base voltage	Open collector	7.5	V
I_C	Collector current (DC)		8	A
I_{CP}	Collector current (Pulse)		15	A
I_B	Base current (DC)		4	A
I_{BM}	Base current (Pulse)		6	A
P_{tot}	Total power dissipation	T_C=25℃	34	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-65~150	℃

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	I_C=100mA ;I_B=0,L=25mH	700			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=1mA ;I_C=0	7.5	13.5		V
V_{CEsat}	Collector-emitter saturation voltage	I_C=4.5A; I_B=1.6A			1.0	V
V_{BEsat}	Base-emitter saturation voltage	I_C=4.5A ;I_B=2A			1.1	V
I_{CES}	Collector cut-off current	V_{CE}=RatedV_{CE}; V_{BE}=0 T_C=125℃			1.0 2.0	mA
I_{EBO}	Emitter cut-off current	V_{EB}=6V; I_C=0			10	mA
h_{FE}	DC current gain	I_C=0.1A ; V_{CE}=5V	6		30	
f_T	Transition frequency	I_C=0.1A ; V_{CE}=5V		7		MHz
C_{OB}	Output capacitance	I_E=0 ; V_{CB}=10V;f=1MHz		125		pF

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PACKAGE OUTLINE

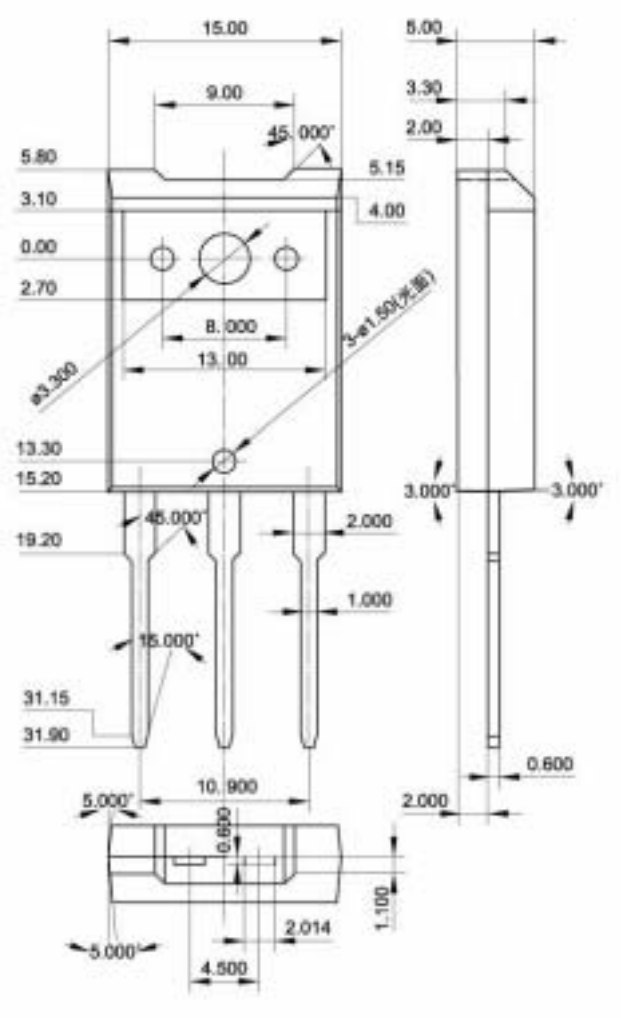

Fig.2 Outline dimensions (unindicated tolerance:±0.30mm)